

# 2SD1260, 2SD1260A

## Silicon NPN triple diffusion planar type Darlington

For power amplification

Complementary to 2SB937 and 2SB937A

### Features

- High forward current transfer ratio  $h_{FE}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	2SD1260	60	V
	2SD1260A	80	
Collector to emitter voltage	2SD1260	60	V
	2SD1260A	80	
Emitter to base voltage	$V_{EBO}$	5	V
Peak collector current	$I_{CP}$	4	A
Collector current	$I_C$	2	A
Collector power dissipation	$T_C=25^\circ\text{C}$	35	W
	$T_a=25^\circ\text{C}$	1.3	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	2SD1260	$V_{CE} = 60\text{V}, I_E = 0$			1	mA
	2SD1260A				1	
Collector cutoff current	2SD1260	$V_{CE} = 30\text{V}, I_B = 0$			2	mA
	2SD1260A				2	
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			2	mA
Collector to emitter voltage	2SD1260	$I_C = 30\text{mA}, I_B = 0$	60			V
	2SD1260A		80			
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 4\text{V}, I_C = 1\text{A}$	1000			
	$h_{FE2}^*$	$V_{CE} = 4\text{V}, I_C = 2\text{A}$	1000		10000	
Base to emitter voltage	$V_{BE}$	$V_{CE} = 4\text{V}, I_C = 2\text{A}$			2.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 8\text{mA}$			2.5	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz
Turn-on time	$t_{on}$	$I_C = 2\text{A}, I_{B1} = 8\text{mA}, I_{B2} = -8\text{mA}, V_{CC} = 50\text{V}$		0.5		$\mu\text{s}$
Storage time	$t_{stg}$		4			$\mu\text{s}$
Fall time	$t_f$		1			$\mu\text{s}$

\* $h_{FE2}$  Rank classification

Rank	R	Q	P
$h_{FE2}$	1000 to 2500	2000 to 5000	4000 to 10000

Internal Connection



